

preliminary

Sonic Fast Recovery Diode

$$V_{RRM} = 1200 \text{ V}$$

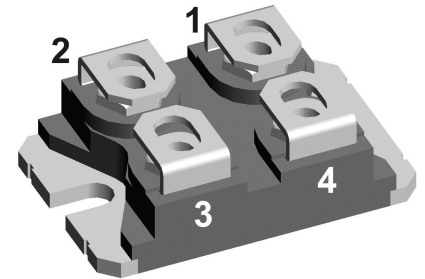
$$I_{FAV} = 2 \times 25 \text{ A}$$

$$t_{rr} = 200 \text{ ns}$$

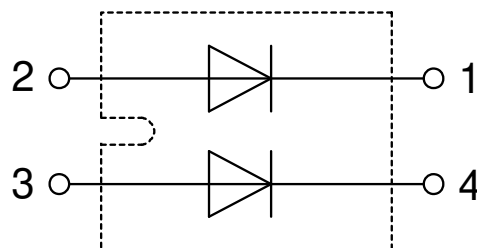
High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Parallel legs

Part number

DHG50X1200NA



Backside: Isolated

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

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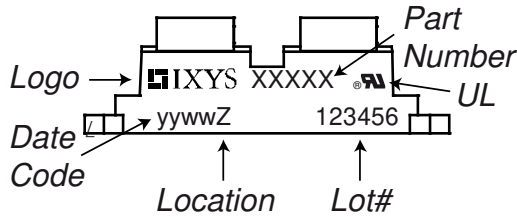


Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
I_R	reverse current, drain current	$V_R = 1200 V$	$T_{VJ} = 25^{\circ}C$		30	μA	
		$V_R = 1200 V$	$T_{VJ} = 125^{\circ}C$		0.5	mA	
V_F	forward voltage drop	$I_F = 25 A$	$T_{VJ} = 25^{\circ}C$		2.11	V	
		$I_F = 50 A$			2.74	V	
		$I_F = 25 A$	$T_{VJ} = 125^{\circ}C$		2.09	V	
		$I_F = 50 A$			2.88	V	
I_{FAV}	average forward current	$T_C = 65^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}C$		25	A	
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		1.23	V	
r_F	slope resistance				30	m Ω	
R_{thJC}	thermal resistance junction to case				1.2	K/W	
R_{thCH}	thermal resistance case to heatsink			0.1		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		100	W	
I_{FSM}	max. forward surge current	$t = 10 ms; (50 Hz), sine; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		200	A	
C_J	junction capacitance	$V_R = 600 V$ $f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		11	pF	
I_{RM}	max. reverse recovery current	} $I_F = 30 A; V_R = 600 V$ $-di_F / dt = 600 A/\mu s$	$T_{VJ} = 25^{\circ}C$		23	A	
			$T_{VJ} = 125^{\circ}C$		30	A	
t_{rr}	reverse recovery time		$T_{VJ} = 25^{\circ}C$		200	ns	
			$T_{VJ} = 125^{\circ}C$		350	ns	



Package SOT-227B (minibloc)		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				30		g
M_D	mounting torque		1.1		1.5	Nm
M_T	terminal torque		1.1		1.5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	10.5	3.2		mm
$d_{Spb/Apb}$		terminal to backside	8.6	6.8		mm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V

Product Marking



Part description

- D = Diode
- H = Sonic Fast Recovery Diode
- G = extreme fast
- 50 = Current Rating [A]
- X = Parallel legs
- 1200 = Reverse Voltage [V]
- NA = SOT-227B (minibloc)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG50X1200NA	DHG50X1200NA	Tube	10	507766

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$

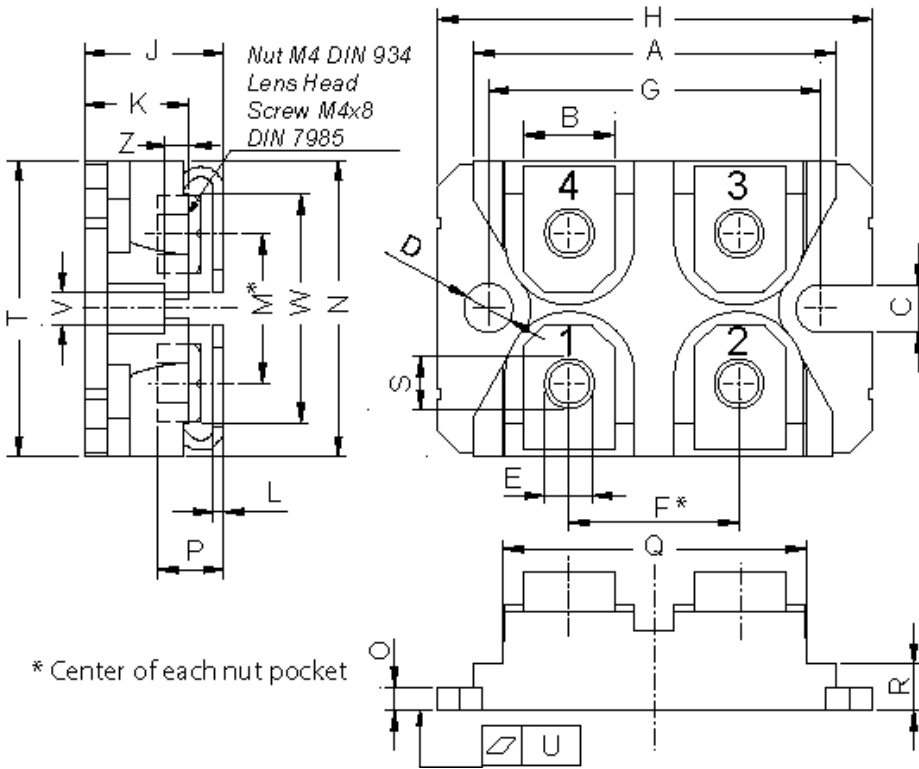


Fast Diode

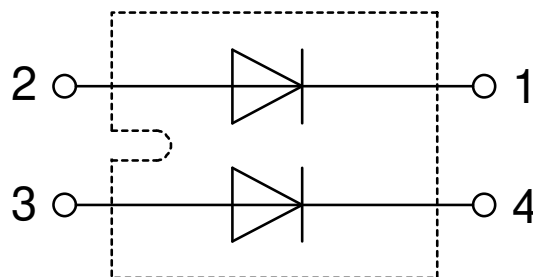
$V_{0\ max}$	threshold voltage	1.23	V
$R_{0\ max}$	slope resistance *	28	mΩ



Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106





Fast Diode

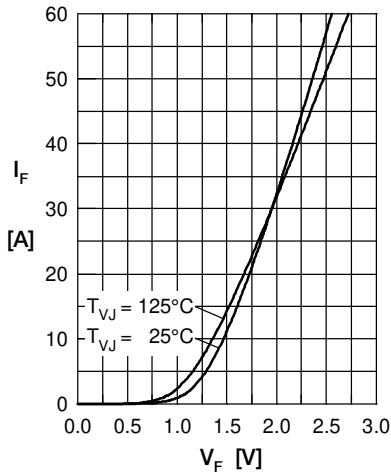


Fig. 1 Typ. Forward current versus V_F

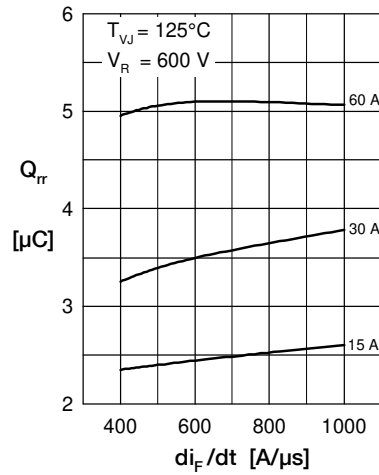


Fig. 2 Typ. reverse recov. charge Q_{rr} versus di/dt

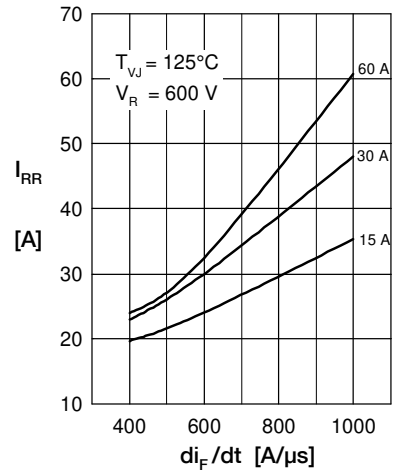


Fig. 3 Typ. peak reverse current I_{RM} versus di/dt

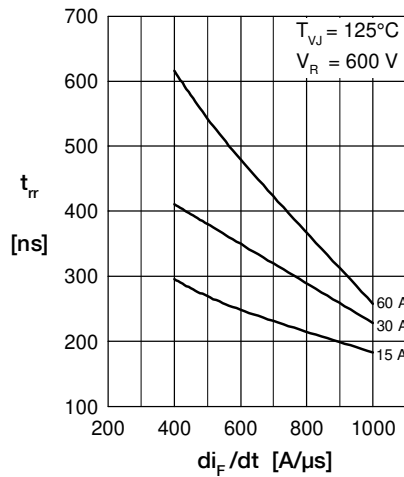


Fig. 4 Dynamic parameters Q_{rr} , I_{RR} versus T_{VJ}

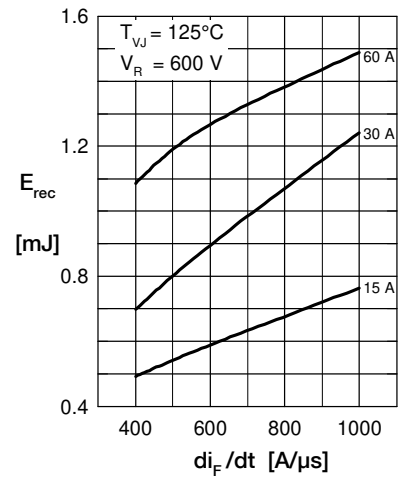


Fig. 5 Typ. recovery energy E_{rec} versus di/dt

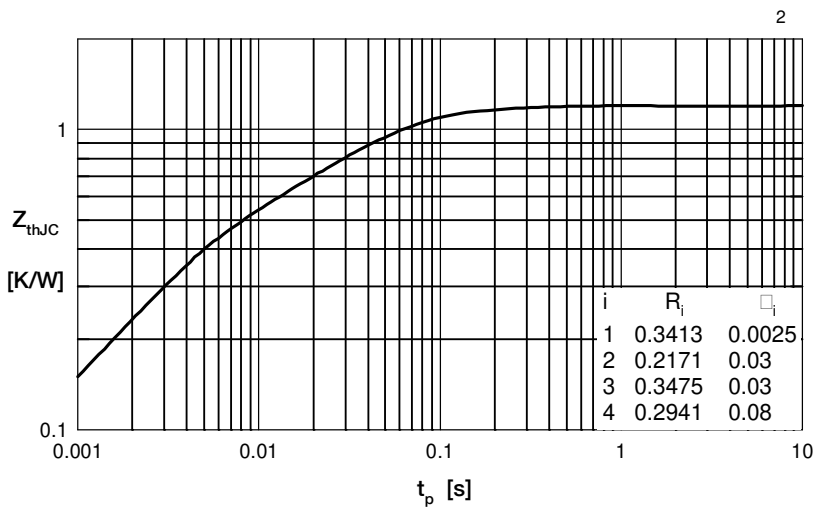


Fig. 6 Typ. recovery energy E_{rec} versus di/dt

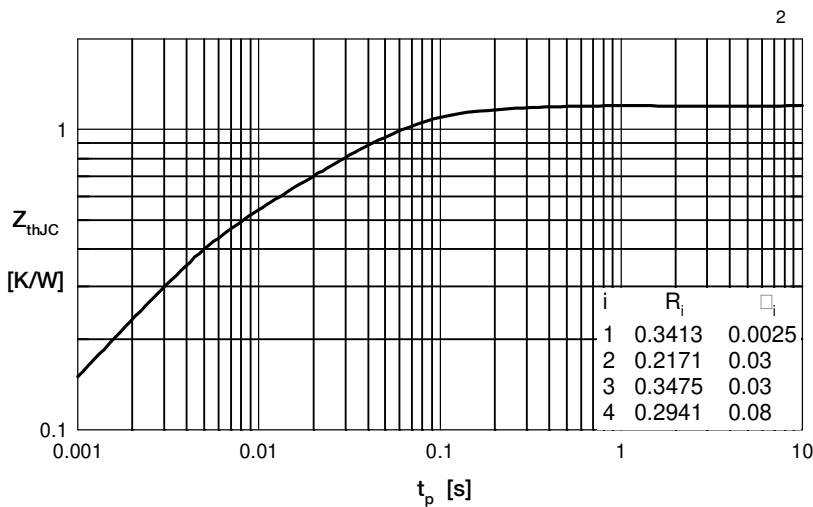


Fig. 7 Typ. transient thermal impedance junction to case